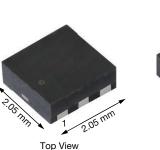
SQA300CEJW

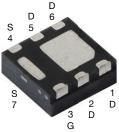
www.vishay.com

Vishay Siliconix

Automotive N-Channel 30 V (D-S) 175 °C MOSFET



Marking Code: QABXXXX



Bottom View

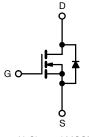
$\begin{tabular}{|c|c|c|c|} \hline PRODUCT SUMMARY \\ \hline V_{DS} (V) & 30 \\ \hline R_{DS(on)} (\Omega) \mbox{ at } V_{GS} = 10 \ V & 0.0330 \\ \hline R_{DS(on)} (\Omega) \mbox{ at } V_{GS} = 4.5 \ V & 0.0540 \\ \hline I_D (A) & 5.63 \\ \hline Configuration & Single \\ \hline \end{tabular}$

PowerPAK[®] SC-70W-6L Single

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- Wettable flank terminals
- 100 % R_{α} and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>





N-Channel MOSFET

_	ORDERING INFORMATION			
	Package	PowerPAK SC-70W-6L		
	Lead (Pb)-free and halogen-free	SQA300CEJW (for detailed order number please see <u>www.vishay.com/doc?79776</u>)		

ABSOLUTE MAXIMUM RATING	GS (T _C = 25 °C, unless	s otherwise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage Gate-source voltage		V _{DS}	30	V
		V _{GS}	± 20	
	T _C = 25 °C	- I _D	5.63	
Continuous drain current ^a	T _C = 125 °C		5.63	
Continuous source current (diode conduction) ^a		I _S	5.63	А
Pulsed drain current ^b		I _{DM}	22.5	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	7	
Single pulse avalanche energy		E _{AS}	2.45	mJ
aximum power dissipation	T _C = 25 °C	D-	13.6	W
	T _C = 125 °C	P _D	4.5	vv
Operating junction and storage temperature	perating junction and storage temperature range		-55 to +175	°C
Soldering recommendations (peak temperations)	iture) ^{d, e}		260	U

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount ^c	R _{thJA}	90	°C/W	
Junction-to-case (drain)		R _{thJC}	11	C/W	

Notes

a. Package limited

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

c. When mounted on 1" square PCB (FR4 material)

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

S23-0325-Rev. A, 15-May-2023

1 For technical questions, contact: <u>automostechsupport@vishav.com</u>

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishav.com/doc?91000

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70W-6L is a leadless package and features wettable flank terminals. The end of the lead terminal is plated with tin.

www.vishay.com

SQA300CEJW Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$		30	-	-	v	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		1.5	2.0	2.5		
Gate-source leakage	I _{GSS}	V _{DS} =	-	-	± 100	nA		
	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 30 V	-	-	1		
Zero gate voltage drain current		$V_{GS} = 0 V$	V _{DS} = 30 V, T _J = 125 °C	-	-	50	μA	
-		$V_{GS} = 0 V$	V _{DS} = 30 V, T _J = 175 °C	-	-	250		
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	5	-	-	Α	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 3 A	-	0.0210	0.0330	Ω	
D · · · · · · · · · · · · · · · · · · ·		V _{GS} = 10 V	I _D = 3 A, T _J = 125 °C	-	-	0.0486		
Drain-source on-state resistance ^a		V _{GS} = 10 V	I _D = 3 A, T _J = 175 °C	-	-	0.0571		
		V _{GS} = 4.5 V	I _D = 2.5 A	-	0.0331	0.0540		
Forward transconductance ^b	g fs		= 15 V, I _D = 3 A	-	16	-	S	
Dynamic ^b	0.0				1		<u> </u>	
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	261	365	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	77	110		
Reverse transfer capacitance	C _{rss}			-	16	23		
Total gate charge ^c	Qq	$V_{GS} = 10 \text{ V}$ $V_{DS} = 15 \text{ V}, I_D = 5 \text{ A}$		-	6	10		
Gate-source charge ^c	Qqs		-	2.0	-	nC		
Gate-drain charge ^c	Q _{gd}		-	2.0	-			
Gate resistance	R _q	f = 1 MHz		2.0	4.2	6.7	Ω	
Turn-on delay time ^c	t _{d(on)}	V_{DD} = 15 V, R _L = 7.5 Ω I _D \cong 2 A, V _{GEN} = 10 V, R _g = 1 Ω		-	6	10	ns	
Rise time ^c	t _r			-	4	8		
Turn-off delay time ^c	t _{d(off)}			-	12	20		
Fall time ^c	t _f			-	2	5		
Source-Drain Diode Ratings and Charact	-	1						
Pulsed current ^a	I _{SM}			-	-	22.5	Α	
Forward voltage	V _{SD}	I _F = 3 A, V _{GS} = 0 V		-	0.84	1.2	V	
Body diode reverse recovery time	t _{rr}	I _F = 2 A, di/dt = 100 A/μs		-	11	22	ns	
Body diode reverse recovery charge	Q _{rr}			-	3	6	nC	
Reverse recovery fall time	ta			-	5	-	- ns	
Reverse recovery rise time	t _b			-	6	-		
Body diode peak reverse recovery current	I _{RM(REC)}			-	-0.5	_	Α	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

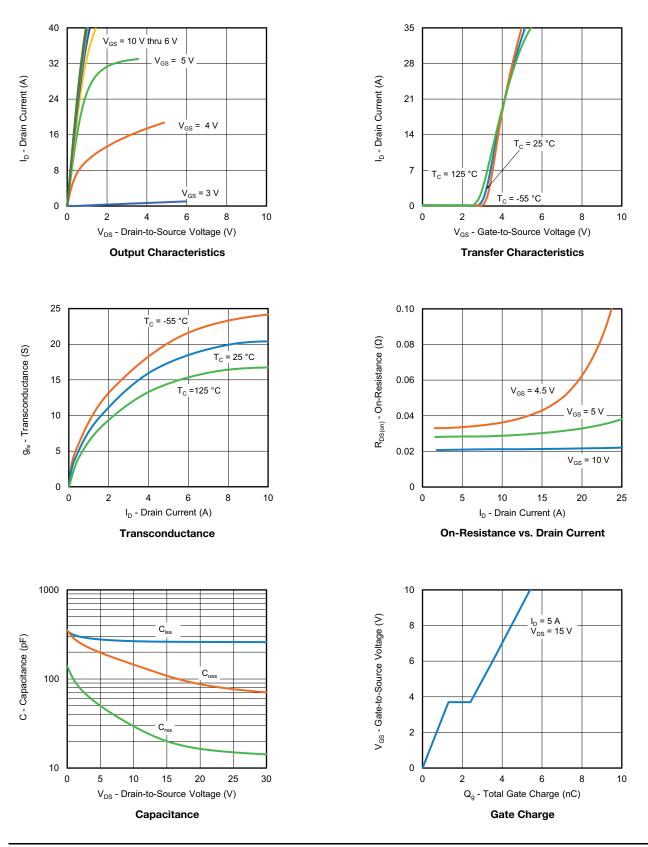
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2



Vishay Siliconix

TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



S23-0325-Rev. A, 15-May-2023

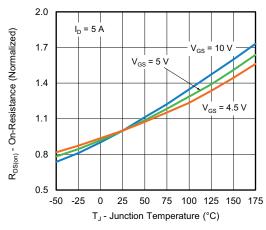
3 stions contact automostechsupp

For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

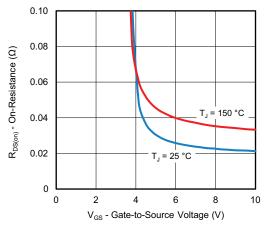


Vishay Siliconix

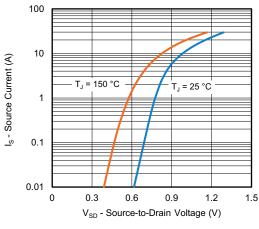
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



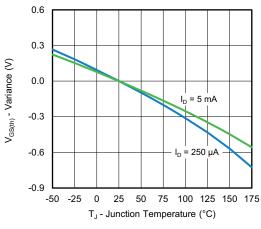
On-Resistance vs. Junction Temperature



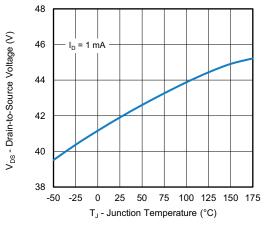
On-Resistance vs. Gate-to-Source Voltage



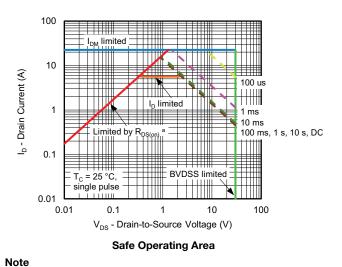
Source Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



a. V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

S23-0325-Rev. A, 15-May-2023

4

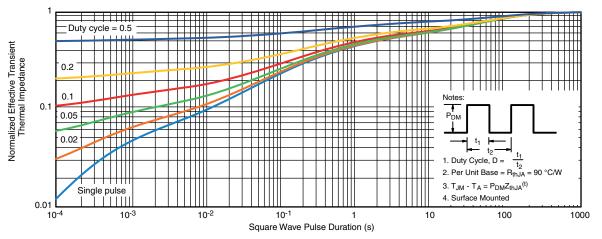
Document Number: 62142

For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

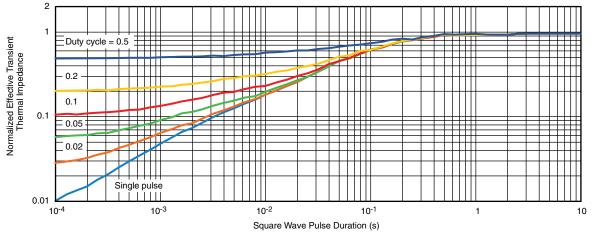


Vishay Siliconix

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62142.



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.